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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. MICRON.098DV1 APPLICATION NO. Unknown

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Basceri et a

FILING DATE Herewith GROUP Unknown 09/971955 09/971955

	U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
On	5,335,138	08/02/94	Sandhu et al.				
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						YES	NO	
			<i>[</i>					
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cn	Hiromi Itoh et al., "Integration of BST Thin Film for Dram Fabrication", Integrated Ferroelectrics, 1995, Vol. 11, pp. 101-109
an	C. Basceri, "An Important Failure Mechanism in MOCVD (Ba,Sr) TiO Thin Films: Resistance Degradation", Ferroelectric Thin Films IV, Materials Research Society, 1998, pp. 9-14
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EXAMINER

DATE CONSIDERED

2-20-03

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